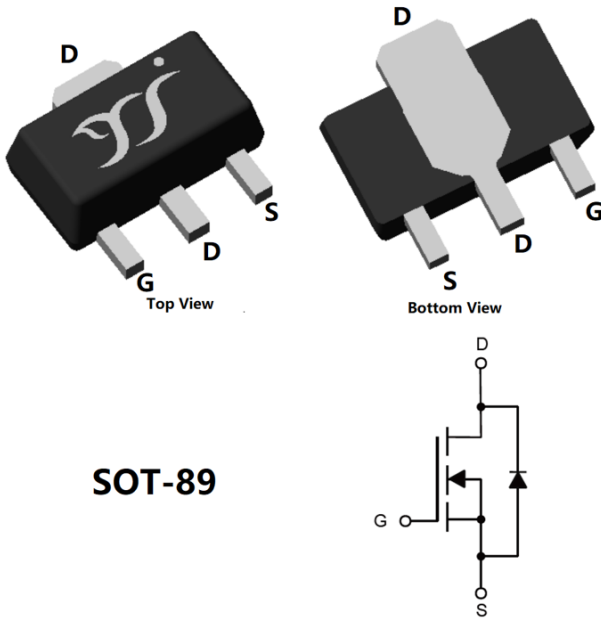


N-Channel Enhancement Mode Field Effect Transistor



SOT-89

Product Summary

- V_{DS} 60V
- I_D 3.0A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 100mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 120mohm

General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ\text{C}$	3
		$T_A=70^\circ\text{C}$	2.4
Pulsed Drain Current ^A	I_{DM}	12	A
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	0.69
		$T_A=70^\circ\text{C}$	0.44
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	180	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJH03N06A	F2	6003A	1000	8000	32000	7" reel



YJH03N06A

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS1}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
	I_{GSS2}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 50	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.3	2.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3A$		86	100	m Ω
		$V_{GS}=4.5V, I_D=2A$		92	120	
Diode Forward Voltage	V_{SD}	$I_S=3A, V_{GS}=0V$			1.2	V
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1\text{MHz}$		409		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			41		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=3A$		10.27		nC
Gate-Source Charge	Q_{gs}			1.65		
Gate-Drain Charge	Q_{gd}			2.11		
Reverse Recovery Charge	Q_{rr}	$I_F=3A, di/dt=100A/\mu s$		6.99		ns
Reverse Recovery Time	t_{rr}			32.6		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=30V, R_L=20\Omega$ $R_{GEN}=3\Omega$		3.6		ns
Turn-on Rise Time	t_r			17.6		
Turn-off Delay Time	$t_{D(off)}$			13		
Turn-off fall Time	t_f			23		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

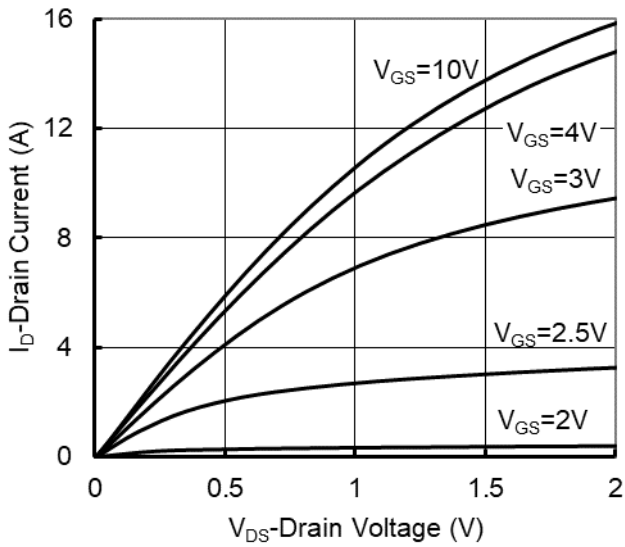


Figure1. Output Characteristics

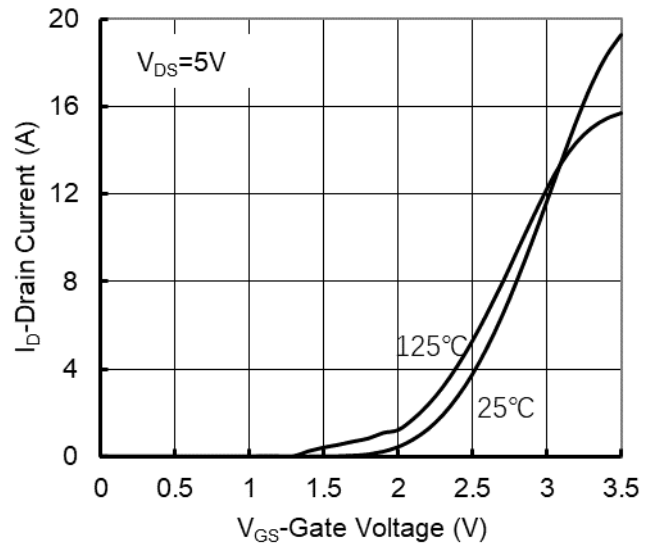


Figure2. Transfer Characteristics

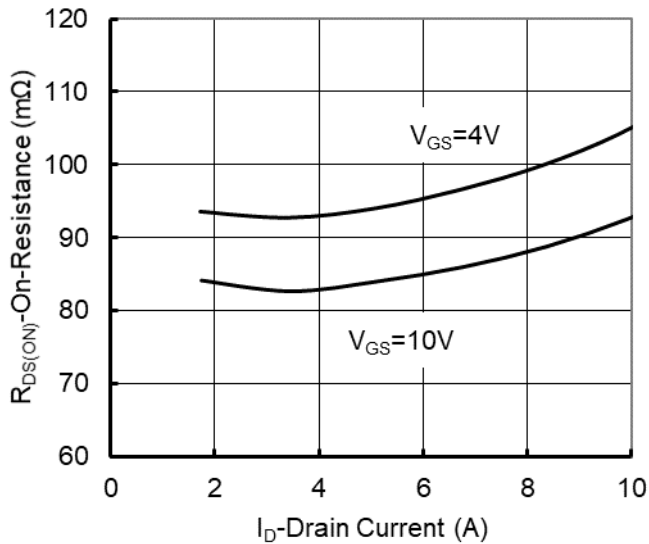


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

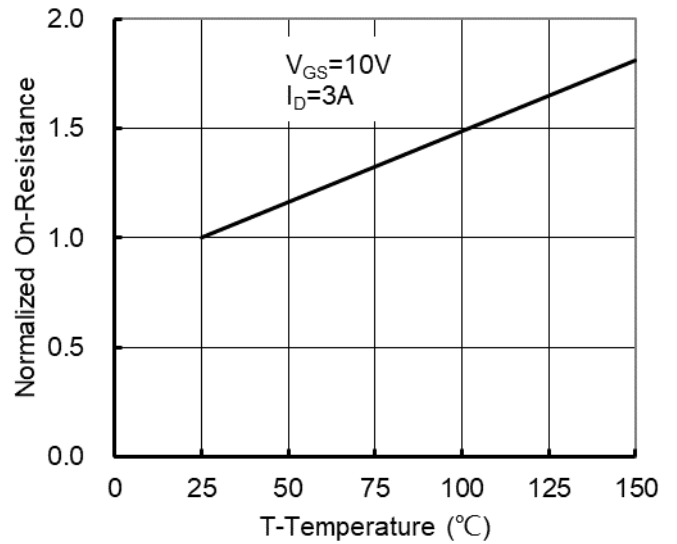


Figure 4: On-Resistance vs. Junction Temperature

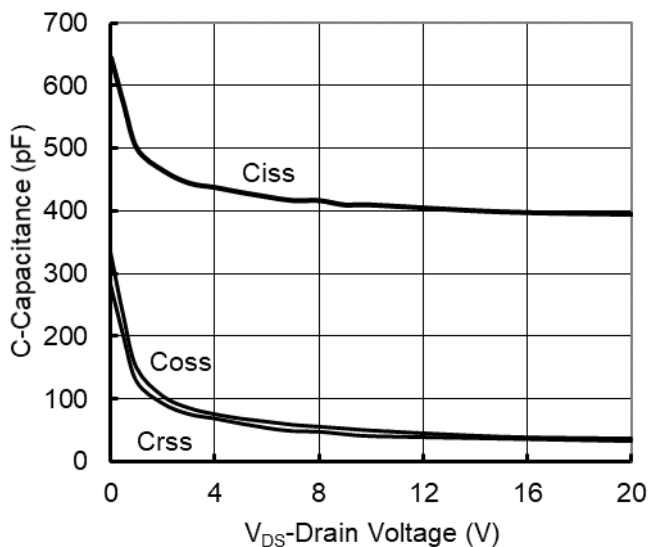


Figure5. Capacitance Characteristics

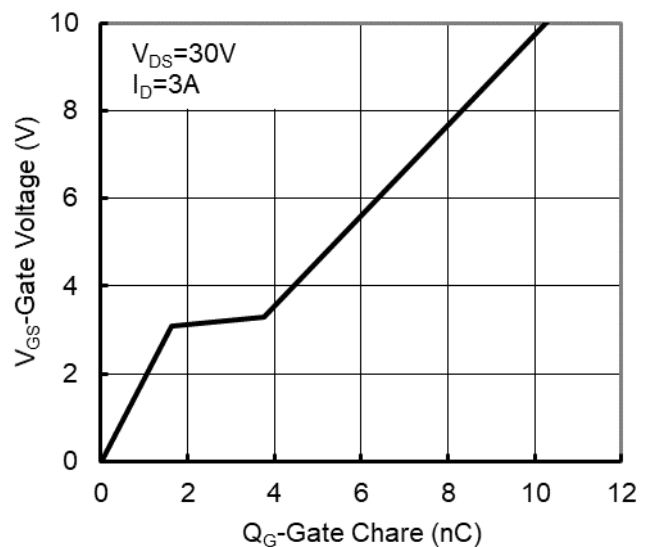


Figure6. Gate Charge



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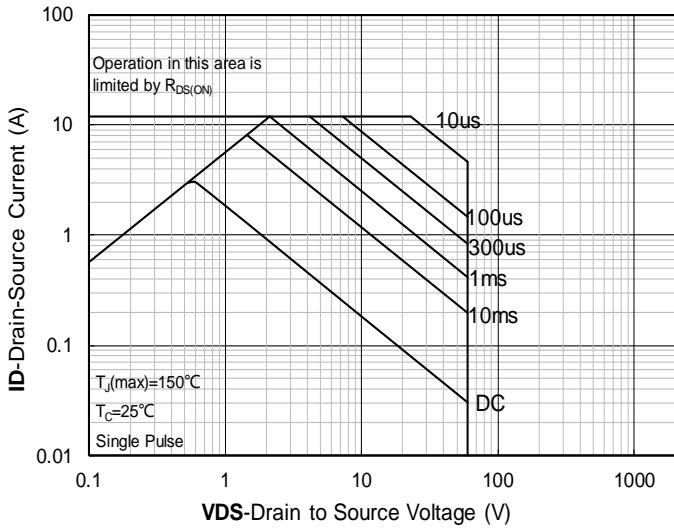


Figure7. Safe Operation Area

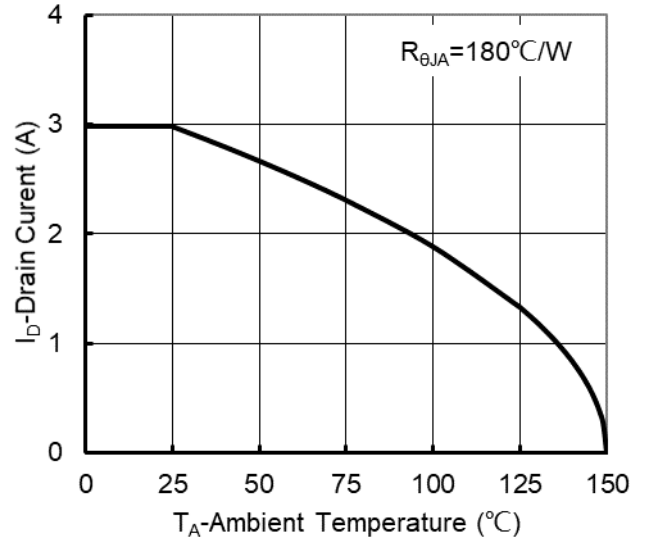


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

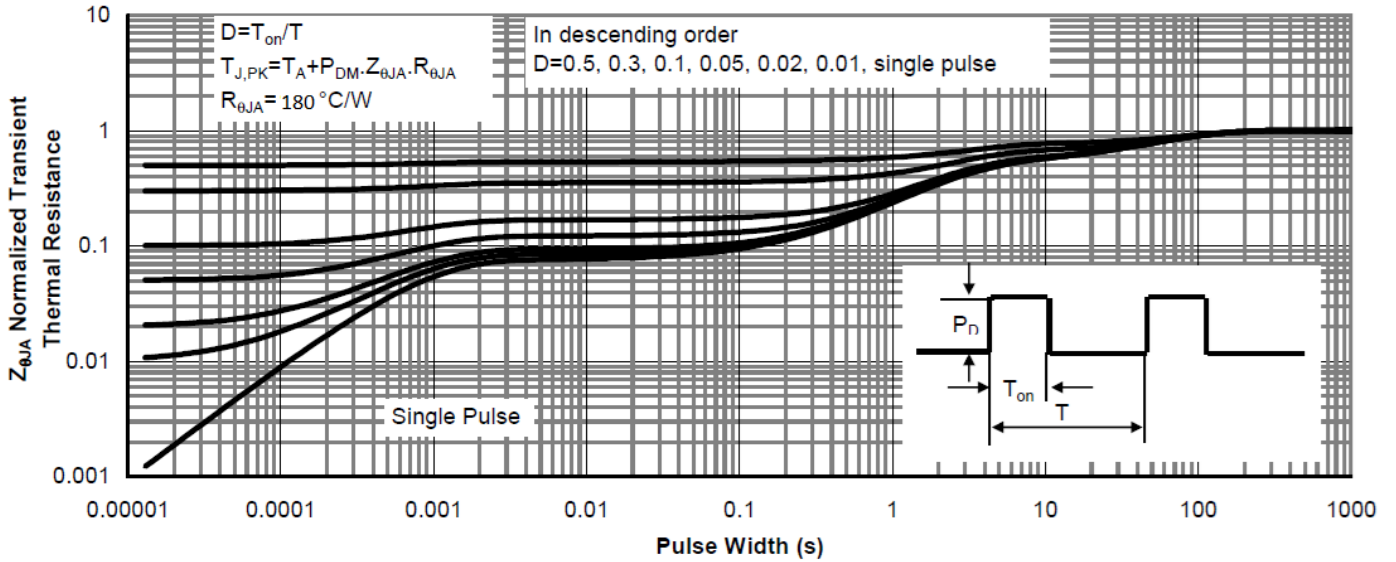
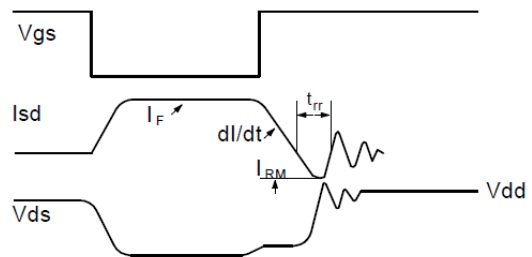
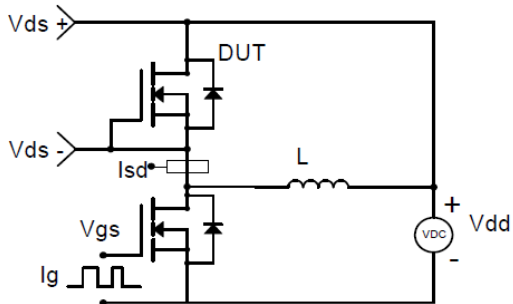


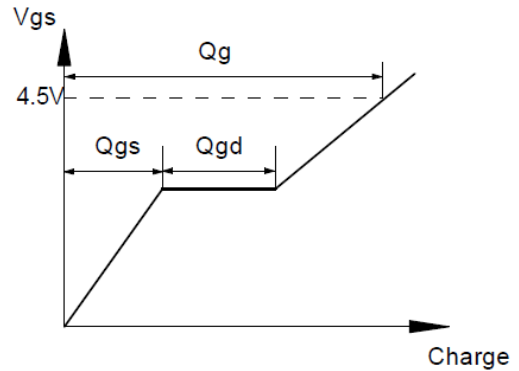
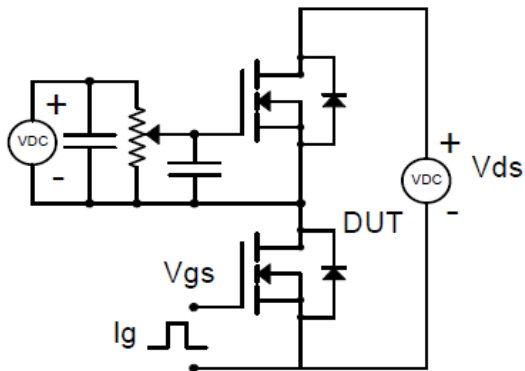
Figure9. Normalized Maximum Transient Thermal Impedance



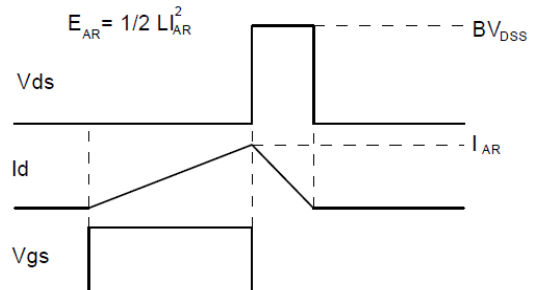
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

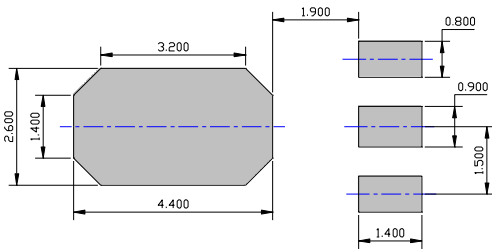
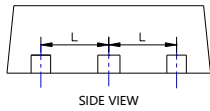
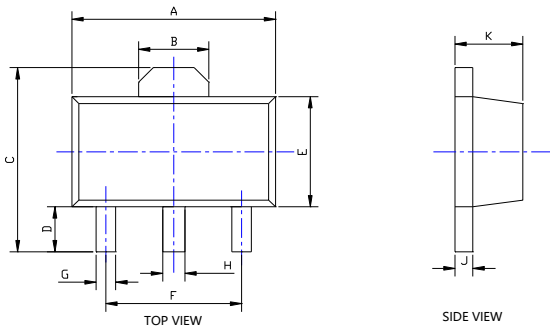


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



YJH03N06A

■ SOT-89 Package Information



SUGGESTED SOLDER PAD LAYOUT

UNIT: mm

DIMENSIONS				
DIM	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.169	0.185	4.300	4.700
B	0.061TYP		1.550TYP	
C	0.154	0.171	3.910	4.350
D	0.031	0.047	0.800	1.200
E	0.089	0.104	2.250	2.650
F	0.118TYP		3.000TYP	
G	0.013	0.020	0.330	0.520
H	0.016	0.023	0.400	0.580
J	0.014	0.017	0.350	0.440
K	0.055	0.063	1.400	1.600
L	0.059TYP		1.500TYP	

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



YJH03N06A

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